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Docket No.: 49657-586

PATENT

MAR 0 7 2002 Technology Center 2100

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Yuichi KUNORI

Serial No.: 09/469,497

Filed: December 22, 1999

Group Art Unit: 2187

Examiner: J. Song

For:

MULTILEVEL STORAGE NONVOLATILE SEMICONDUCTOR MEMORY DEVICE ENABLING

HIGH-SPEED DATA READING AND HIGH-SPEED DATA WRITING

THE COMMISSIONER FOR PATENTS AND TRADEMARKS Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	17	20	0	\$18.00 =	\$0.00
Independent Claims	4	3	1	\$84.00 =	\$84.00
		Multiple claims newly presented			\$0.00
		Fee for extension of time			\$0.00
					\$0.00
Total of Above Calculations				\$84.00	

Please charge my Deposit Account No. <u>500417</u> in the amount of \$84.00. An additional copy of this transmittal sheet is submitted herewith.

The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

03/05/2002 JBALINAN 00000052 500417 09469497

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MCDERMOTT, WILL & EMERY

Gene Z. Rubinson

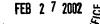
Registration No. 33,351

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(202) 756-8000 GZR:cms

Date: February 27, 2002 Facsimile: (202) 756-8087

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MULTILEVEL STORAGE NONVOLATILE SEMICONDUCTOR MEMORY DEVICE ENABLING HIGH-SPEED DATA READING AND HIGH-SPEED

DATA WRITING

PRELIMINARY AMENDMENT

Commissioner for Patents Washington, DC 20231

Sir:

Please amend the above-identified application, prior to examination thereof, as follows:

IN THE CLAIMS

Please add the following new claims to the application:

-- 13. A method for reading a plurality of data from a non-volatile semiconductor memory device, said non-volatile semiconductor memory device including a memory cell storing said plurality of data and a data output node for outputting said data, said method comprising the steps of:

reading a part of said plurality of data from said memory cell;

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